Product Brief

CoolSiC™ MOSFET. Revolution to rely on.

Infineon’s CoolSiC™ technology enables radical new product designs.

Silicon Carbide (SiC) opens up new degrees of freedom for designers to harness never before seen levels of efficiency and system flexibility. In comparison to traditional silicon (Si) based switches like IGBTs and MOSFETs, the SiC MOSFET offers a series of advantages. These include, the lowest gate charge and device capacitance levels seen in 1200 V switches, no reverse recovery losses of the internal commutation proof body diode, temperature independent low switching losses, and threshold-free on-state characteristics. Infineon’s unique 1200 V SiC MOSFET adds additional advantages. Superior gate oxide reliability enabled by state-of-the-art trench design, best in class switching and conduction losses, highest transconductance level (gain), threshold voltage of $V_{th} = 4$ V and short-circuit robustness. This is the revolution you can rely on.

All this results in a robust SiC MOSFET, ideal for hard- and resonant-switching topologies like LLC and ZVS converters, which can be driven like an IGBT using standard drivers. Delivering the highest level efficiency at switching frequencies unreachable by Si based switches allowing for system size reduction, power density increases and high lifetime reliability.

Key features
- Low device capacitances
- Temperature independent switching losses
- Intrinsic diode with low reverse recovery charge
- Threshold-free on-state characteristics

Advantages
- Superior gate oxide reliability
- Best in class switching and conduction losses
- IGBT compatible driving (+15 V)
- Threshold voltage, $V_{th} = 4$ V
- Short-circuit robustness

Benefits
- Highest efficiency for reduced cooling effort
- Longer lifetime and higher reliability
- Higher frequency operation
- Reduction in system cost
- Increased power density
- Reduced system complexity
- Ease of design and implementation

Applications
- Photo-Voltaic inverters (PV)
- Energy storage / Battery charging
- Un-interruptable Power Supplies (UPS)
- Switch Mode Power Supplies (SMPS)
- Industrial drives
- Medical

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CoolSiC™ MOSFET first products are targeted for photovoltaic inverters, battery charging and energy storage. TO-247 4pin package contains an additional connection to the source (Kelvin connection) that is used as a reference potential for the gate driving voltage, thereby eliminating the effect of voltage drops over the source inductance. The result is even lower switching losses than for TO-247 3pin version, especially at higher currents and higher switching frequencies.

Easy1B modules offer a very good thermal interface, a low stray inductance and robust design as well as PressFIT connections. The products portfolio will be extended within the next years. The first step is a roll-out of different topologies like Sixpack and Halfbridge covering a power range from 2 kW until 200 kW.

Gate driver selection

Ultrafast switching 1200 V power transistors such as CoolSiC™ MOSFETs can be easier handled by means of isolated gate output sections. Therefore, galvanically isolated gate driver ICs based on Infineon’s coreless transformer technology are recommended as most suitable.

The drivers incorporate most important key features and parameters for SiC MOSFET driving such as tight propagation delay matching, precise input filters, wide output side supply range, negative gate voltage capability, and extended CMTI capability.

Lead products

<table>
<thead>
<tr>
<th>Schematic</th>
<th>Type</th>
<th>( R_{\text{ds(on)}} ) [mΩ]</th>
<th>( V_{DSS} ) [V]</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>Single switch</td>
<td>IMW120R045M1</td>
<td>45</td>
<td>1200</td>
<td>TO-247 3pin</td>
</tr>
<tr>
<td>Single switch</td>
<td>IMZ120R045M1</td>
<td>45</td>
<td>1200</td>
<td>TO-247 4pin</td>
</tr>
<tr>
<td>Booster with NTC</td>
<td>DF11MR12W1M1_B11</td>
<td>11</td>
<td>1200</td>
<td>Easy1B</td>
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<tr>
<td>Booster with NTC</td>
<td>DF23MR12W1M1_B11</td>
<td>23</td>
<td>1200</td>
<td></td>
</tr>
<tr>
<td>Half-bridge with NTC</td>
<td>FF11MR12W1M1_B11</td>
<td>11</td>
<td>1200</td>
<td></td>
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<tr>
<td>Half-bridge with NTC</td>
<td>FF23MR12W1M1_B11</td>
<td>23</td>
<td>1200</td>
<td></td>
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</table>

Samples available

Roll-out products phase 1

<table>
<thead>
<tr>
<th>Schematic</th>
<th>Type</th>
<th>( R_{\text{ds(on)}} ) [mΩ]</th>
<th>( V_{DSS} ) [V]</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>SixPACK with NTC</td>
<td>FS45MR12W1M1_B11</td>
<td>45</td>
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<td>Easy1B</td>
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<td>Half-bridge with NTC</td>
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<td>1200</td>
<td>Easy2B</td>
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<td>Half-bridge</td>
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<td>6</td>
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<td>62 mm</td>
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</tbody>
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Selectively sampling in 2017

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Published by
Infineon Technologies AG
81726 Munich, Germany

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Order Number: B133-10286-V2-7600-EU-EC-P
Date: 05/2017

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